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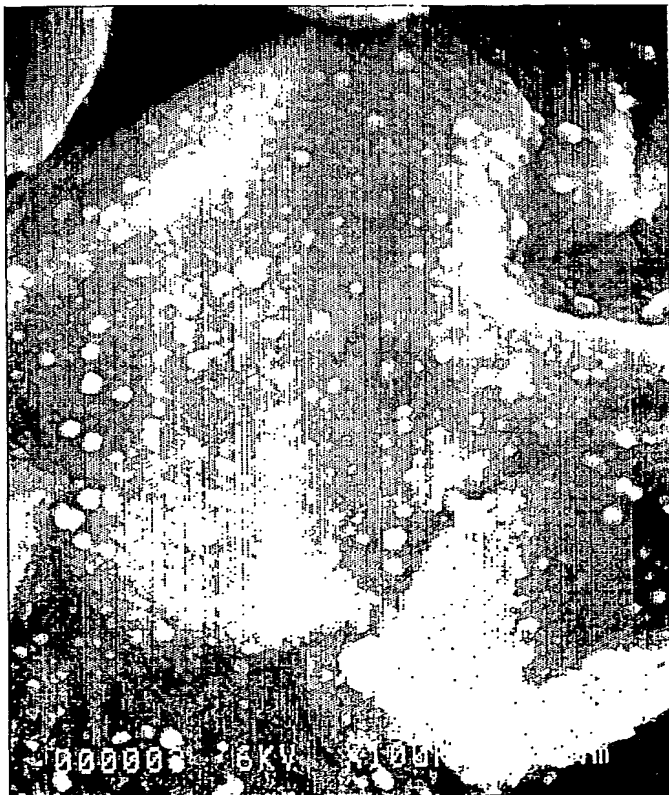
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(54) Title: PRODUCTION METHOD OF A CAPACITOR



(57) Abstract: The present invention relates to a method for producing a capacitor comprising, as one electrode, an electric conductor having formed on the surface thereof a dielectric layer and, as the other electrode, a semiconductor layer formed on the electric conductor by energization using the electric conductor as the anode, wherein fine protrusions are formed on the dielectric layer before energization; a capacitor produced by the method thereof having a good capacitance appearance factor and a low ESR; and an electronic circuit and an electronic device using the capacitor.

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